

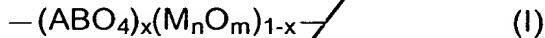
In re: Lucovsky et al
Serial No.: 09/891,552
Filed: June 25, 2001
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oxide layer. Gusev *et al.* propose that it is possible to deposit aluminum oxide on hydrogen-terminated silicon without forming an interfacial layer using NRP, medium energy ion scattering (MEIS), and high-resolution transmission electron microscopy (TEM).--

In the Claims:

Please replace Claim 1 with the following amended claim:

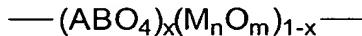
1. (Amended) A non-crystalline oxide represented by the formula (I):



wherein:
A is an element selected from Group IIIA of the periodic table;
B is an element selected from Group VB of the periodic table;
O is oxygen;
M is an element selected from either Group IIIB or Group IVB of the periodic table; and
n ranges from about 0.5 to about 2.5, m ranges from about 1.5 to about 3.5, and
 $0 < x < 1$.

Please replace Claim 4 with the following amended claim:

4. (Amended) A method of forming a non-crystalline oxide represented by the formula (I):



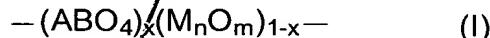
wherein A is an element selected from Group IIIA of the periodic table, B is an element selected from Group VB of the periodic table, O is oxygen, M is an element selected from either Group IIIB or Group IVB of the periodic table, n ranges from about 0.5 to about 2.5, m ranges from about 1.5 to about 3.5, and $0 < x < 1$, said method comprising:

delivering a gaseous source comprising element A, a gaseous source comprising element B, a gaseous source comprising element M, and a gaseous source comprising oxygen on a substrate such that the gaseous source comprising element A, the gaseous source comprising

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element B, the gaseous source comprising element M, and the gaseous source comprising oxygen react to form the non-crystalline oxide.

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Please replace Claim 11 with the following amended claim:

11. (Amended) A field effect transistor comprising:
an integrated circuit substrate having a first surface;
source and drain regions in said substrate at said first surface in a
spaced apart relationship; and
a gate insulating layer on said substrate at said first surface between said spaced apart
source and drain regions, said gate insulating layer comprising a non-crystalline oxide
represented by the formula (I):

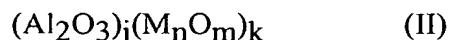


wherein:

A is an element selected from Group IIIA of the periodic table;
B is an element selected from Group VB of the periodic table;
O is oxygen;
M is an element selected from either Group IIIB or Group IVB of the periodic table;
n ranges from about 0.5 to about 2.5;
m ranges from about 1.5 to about 3.5; and
 $0 < x < 1$.

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Please replace Claim 24 with the following amended claim:

24. (Amended) A non-crystalline oxide represented by the formula (II):



wherein:

Al is aluminum;